

FIG. 2A

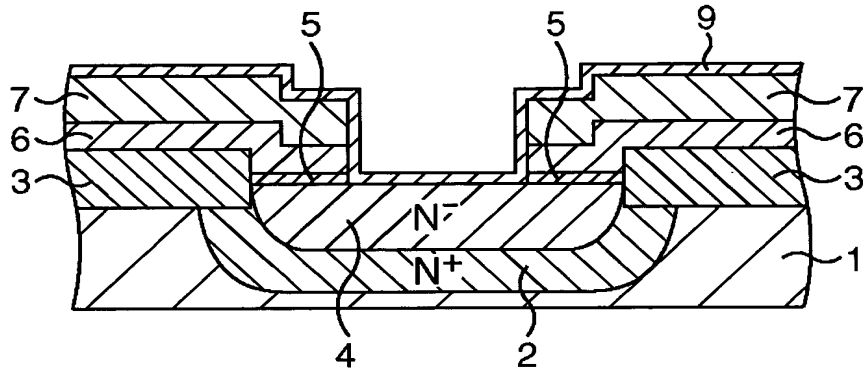


FIG. 2B

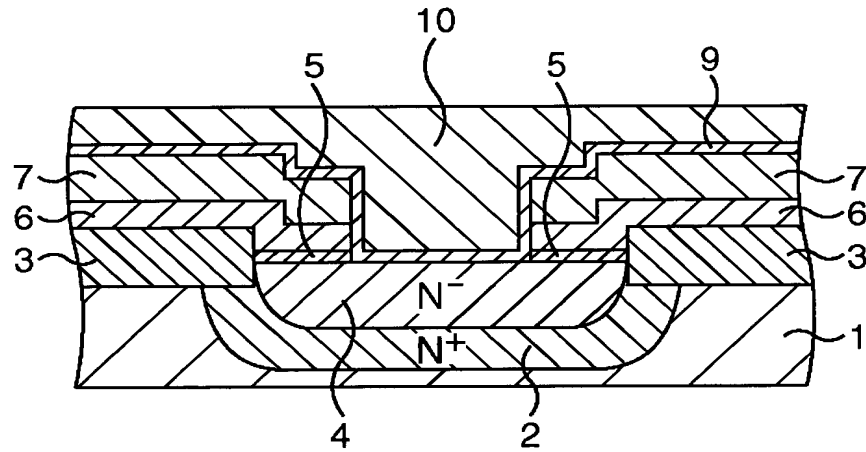
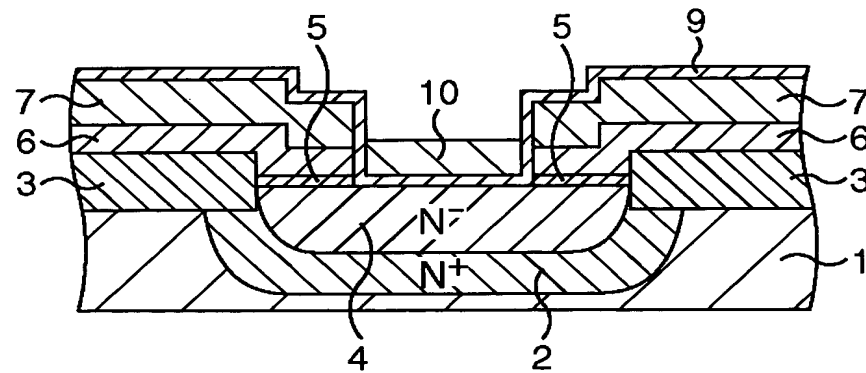


FIG. 2C



A cross-sectional view of a semiconductor device. The device consists of a substrate with multiple layers labeled 1, 2, 3, 6, and 7. A central region contains two distinct areas labeled N^- and N^+ . A large, irregularly shaped region is labeled 11. Other regions are labeled 2, 4, 5, 9, and 10.

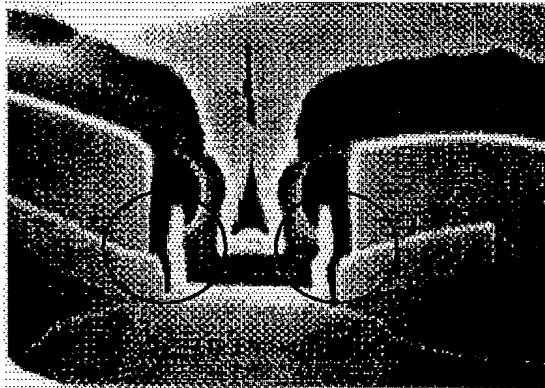


FIG. 6

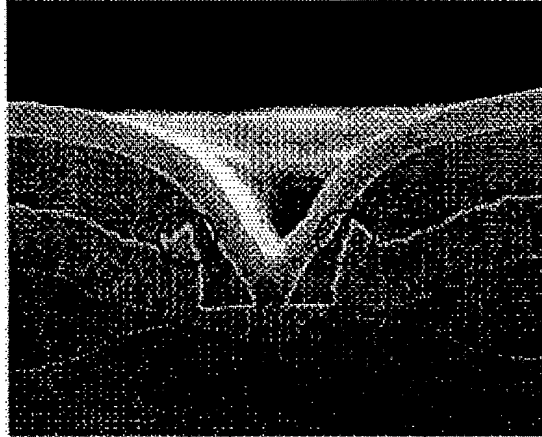


FIG. 7

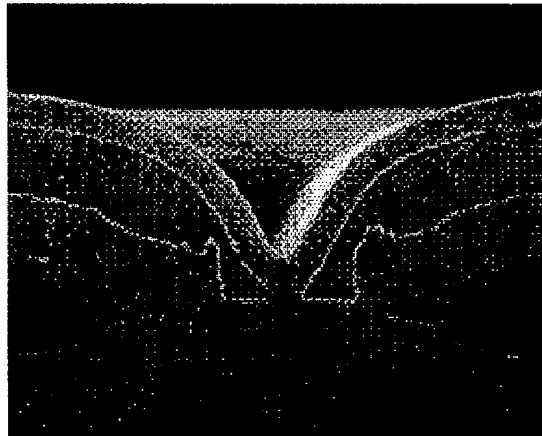


FIG. 8

